











INA118

SBOS027A - SEPTEMBER 2000 - REVISED JANUARY 2016

INA118 Precision, Low Power Instrumentation Amplifier

Features

Low Offset Voltage: 50-µV Maximum

Low Drift: 0.5-µV/°C Maximum

Low Input Bias Current: 5-nA Maximum

High CMR: 110-dB Minimum Inputs Protected to ±40 V

Wide Supply Range: ±1.35 to ±18 V Low Quiescent Current: 350-µA

8-Pin Plastic DIP, SO-8

Applications

- **Bridge Amplifiers**
- Thermocouple Amplifiers
- **RTD Sensor Amplifiers**
- Medical Instrumentation
- **Data Acquisition**

3 Description

The INA118 is a low-power, general-purpose instrumentation amplifier offering excellent accuracy. The device's versatile, 3-op amp design and small size make it ideal for a wide range of applications. Current-feedback input circuitry provides wide bandwidth, even at high gain (70 kHz at G = 100).

A single external resistor sets any gain from 1 to 10000. Internal input protection can withstand up to ±40 V without damage.

The INA118 is laser-trimmed for low offset voltage (50 μ V), drift (0.5 μ V/°C), and high common-mode rejection (110 dB at G = 1000). The INA118 operates with power supplies as low as ±1.35 V, and quiescent current is only 350 µA, making the device ideal for battery-operated systems.

The INA118 is available in 8-pin plastic DIP and SO-8 surface-mount packages, specified for the -40°C to +85°C temperature range.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
INIAAAO	SOIC (8)	3.91 mm × 4.90 mm
INA118	PDIP (8)	6.35 mm × 9.81 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Schematic

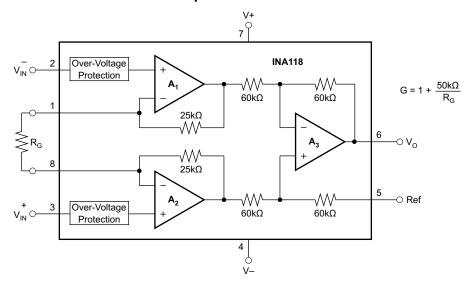




Table of Contents

1	Features 1	8 Application and Implementation 1
2	Applications 1	8.1 Application Information 1
3	Description 1	8.2 Typical Application1
4	Revision History2	9 Power Supply Recommendations 1
5	Pin Configuration and Functions 3	9.1 Low Voltage Operation 1
6	Specifications4	9.2 Single Supply Operation 1
•	6.1 Absolute Maximum Ratings 4	10 Layout 1
	6.2 ESD Ratings	10.1 Layout Guidelines 1
	6.3 Recommended Operating Conditions	10.2 Layout Example2
	6.4 Thermal Information	11 Device and Documentation Support 2
	6.5 Electrical Characteristics5	11.1 Device Support2
	6.6 Typical Characteristics 7	11.2 Documentation Support
7	Detailed Description 11	11.3 Community Resources 2
•	7.1 Overview	11.4 Trademarks2
	7.2 Functional Block Diagram	11.5 Electrostatic Discharge Caution 2
	7.3 Feature Description	11.6 Glossary
	7.4 Device Functional Modes	12 Mechanical, Packaging, and Orderable Information

4 Revision History

Changes from Original (September 2000) to Revision A

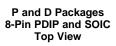
Page

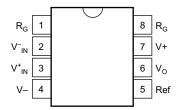
Added ESD Ratings table, Feature Description section, Device Functional Modes section, Application and
Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation
Support section, and Mechanical, Packaging, and Orderable Information section.

Submit Documentation Feedback Copyright © 2000–20



5 Pin Configuration and Functions





Pin Functions

	PIN				DESCRIPTION	
NO.	NAME	I/O				
1	R _G	_	Gain setting pin. For gains greater than 1, place a gain resistor between pin 1 and pin 8.			
2	V ⁻ IN	I	Negative input			
3	V ⁺ IN	1	Positive input			
4	V-	_	Negative supply			
5	Ref	I	Reference input. This pin must be driven by low impedance or connected to ground.			
6	Vo	0	Output			
7	V ⁺	_	Positive supply			
8	R _G	_	Gain setting pin. For gains greater than 1, place a gain resistor between pin 1 and pin 8.			

Copyright © 2000–2016, Texas Instruments Incorporated



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
	Supply voltage		±18	V
	Analog input voltage		±40	V
	Output short-circuit (to ground)	Conti	nuous	
	Operating temperature	-40	125	°C
	Junction temperature		150	°C
	Lead temperature (soldering, 10 s)		300	°C
T _{stg}	Storage temperature	-40	125	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±1000	
$V_{(ESD)}$	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±500	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V	Power supply	±2.25	±15	±18	٧
$V_O = 0$	Input common-mode voltage	V ⁻ + 1.1		V ⁺ - 1	٧
T _A	Ambient temperature	– 55		150	ů

6.4 Thermal Information

			INA118		
	THERMAL METRIC ⁽¹⁾	D (SOIC)	P (PDIP)	UNIT	
		8 PINS	8 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	115	48	°C/W	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	62	37	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	59	25	°C/W	
ΨЈТ	Junction-to-top characterization parameter	14	14	°C/W	
ΨЈВ	Junction-to-board characterization parameter	58	25	°C/W	
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W	

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

Product Folder Links: INA118

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.5 Electrical Characteristics

at $T_A = 25$ °C, $V_S = \pm 15$ V, $R_L = 10$ k Ω unless otherwise noted.

at $T_A = 25^{\circ}C$, $V_S = \pm 1$		TEST CON		MIN	TYP	MAX	UNIT
INPUT							
			INA118PB, UB		±10 ± 50/G	±50 ± 500/G	
	Initial	T _A = 25°C	INA118P, U		±25 ±100/G	±125±1000/	μV
			INA118PB, UB		±0.2 ± 2/G	±0.5 ± 20/G	μV/°C
Offset voltage, RTI	vs Temperature	$T_A = T_{MIN}$ to T_{MAX}	INA118P, U		±0.2 ± 5/G	±1 ± 20/G	
			INA118PB, UB		±1 ±10/G	±5 ± 100/G	
	vs Power supply	$V_S = \pm 1.35 \text{ V to } \pm 18 \text{ V}$	INA118P, U		±1 ±10/G	±10 ±100/G	μV/V
	Long-term stability				±0.4 ±5/G		μV/mo
	Differential				10 ¹⁰ 1		
Impedance	Common-mode				10 ¹⁰ 4		Ω pF
Linear input voltage range				(V+) - 1	(V ⁺) - 0.65		V
Linear input voltage range				(V ⁻) + 1.1	$(V^{-}) + 0.95$		V
Safe input voltage						±40	V
		$V_{CM} = \pm 10 \text{ V}, \Delta R_{S} = 1$	INA118PB, UB	80	90		
		$k\Omega$, $G = 1$	INA118P, U	73	90		
		$V_{CM} = \pm 10 \text{ V}, \Delta R_{S} = 1$	INA118PB, UB	97	110		
Common-mode rejection	Common-mode rejection		INA118P, U	89	110		dB
Common-mode rejection		$V_{CM} = \pm 10 \text{ V}, \ \Delta R_{S} = 1 $ $k\Omega, \ G = 100$	INA118PB, UB	107	120		uв
			INA118P, U	98	120		
		$V_{CM} = \pm 10 \text{ V}, \ \Delta R_{S} = 1 $ $k\Omega, \ G = 1000$	INA118PB, UB	110	125		-
			INA118P, U	100	125		
BIAS CURRENT			INA118PB, UB		±1	±5	nA
BIAS CORRENT			INA118P, U		±1	±10	IIA
vs temperature					±40		pA/°C
OFFSET CURRENT			INA118PB, UB		±1	±5	nA
			INA118P, U		±1	±10	
vs temperature					±40		pA/°C
NOISE VOLTAGE, RTI	T		ı				
	f = 10 Hz				11		nV/√Hz
	f = 100 Hz	$G = 1000, R_S = 0 Ω$			10		nV/√Hz
	f = 1 kHz				10		nV/√Hz
	f _B = 0.1 Hz to 10 Hz				0.28		μVp-p
	f = 10 Hz	-			2		pA/√Hz
Noise current	f = 1 kHz	_			0.3		•
GAIN	$f_B = 0.1 \text{ Hz to } 10 \text{ Hz}$				80		рАр-р
Gain equation					1 + (50 kΩ/R _G)		V/V
Range of gain				1	(50 1/1/13)	10000	V/V
. tango or gain		G = 1		•	±0.01%	±0.024%	V / V
Gain error		G = 10			±0.02%	±0.4%	
		G = 100			±0.05%	±0.5%	
		G = 1000			±0.5%	±1%	
Gain vs temperature		G = 1			±1	±10	ppm/°C
50-kΩ resistance ⁽¹⁾					±25	±100	ppm/°C
**		G = 1			±0.0003	±0.001	
		G = 10			±0.0005	±0.002	
Nonlinearity		G = 100			±0.0005	±0.002	% of FSR
		G = 1000			±0.002	±0.01	
		G = 1000					

⁽¹⁾ Temperature coefficient of the $50\text{-}k\Omega$ term in the gain equation.



Electrical Characteristics (continued)

at T_A = 25°C, V_S = ±15 V, R_L = 10 k Ω unless otherwise noted.

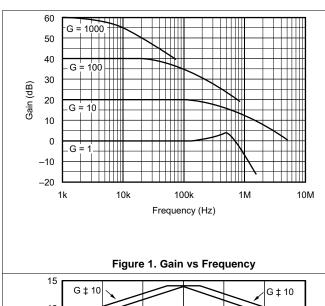
PARA	AMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OUTPUT			'				
	Positive	5 4010	(V ⁺) - 1	(V+) - 0.8			
\/=\k====	Negative	$R_L = 10 \text{ k}\Omega$	(V ⁻) + 0.35	(V ⁻) + 0.2		V	
Voltage: Single supply high		V 0.7.V(0.V(2) D 40.1.0	1.8	2			
	Single supply low	$V_S = 2.7 \text{ V/0 V}^{(2)}, R_L = 10 \text{ k}\Omega$	60	35		mV	
Load capacitance stabil	ity			1000		pF	
Short circuit current				+5/–12		mA	
FREQUENCY RESPON	ISE						
		G = 1		800		kHz	
Donatuidth 2 dD		G = 10	500				
Bandwidth, –3 dB		G = 100		70 7		КПZ	
		G = 1000					
Slew rate		V _O = ±10 V, G = 10		0.9		V/µs	
		G = 1		15			
Cattling time 0.040/		G = 10		15			
Settling time, 0.01%		G = 100		21		μs	
		G = 1000		210			
Overload recovery		50% Overdrive		20		μs	
POWER SUPPLY							
Voltage range			±1.35	±15	±18	V	
Current		V _{IN} = 0 V		±350	±385	μA	
TEMPERATURE RANG	BE .						
Specification			-40		85	°C	
Operating			-40		125	°C	

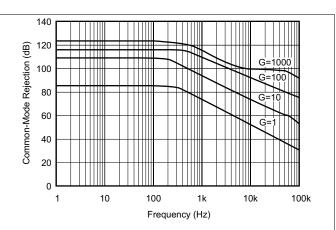
⁽²⁾ Common-mode input voltage range is limited. See text for discussion of low power supply and single power supply operation.

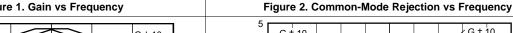


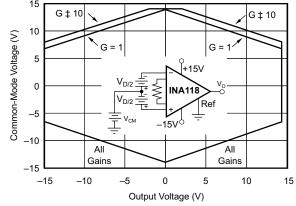
6.6 Typical Characteristics

at $T_A = 25$ °C, $V_S = \pm 15$ V (unless otherwise noted).









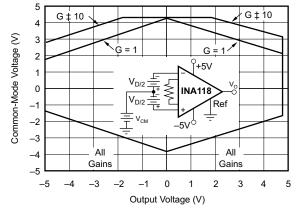
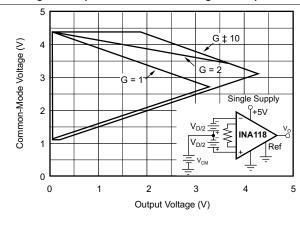


Figure 3. Input Common-Mode Range vs Output Voltage

Figure 4. Input Common-Mode Range vs Output Voltage



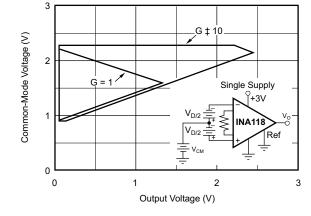


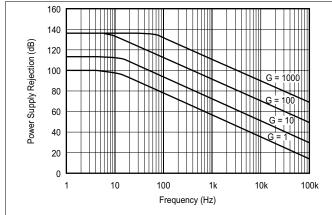
Figure 5. Input Common-Mode Range vs Output Voltage

Figure 6. Input Common-Mode Range vs Output Voltage

TEXAS INSTRUMENTS

Typical Characteristics (continued)

at $T_A = 25$ °C, $V_S = \pm 15$ V (unless otherwise noted).



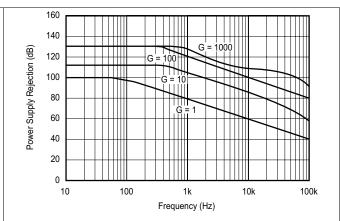
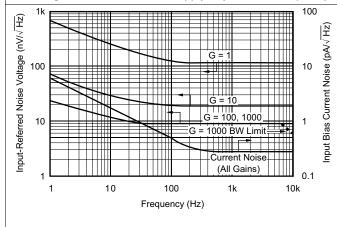


Figure 7. Positive Power Supply Rejection vs Frequency

Figure 8. Negative Power Supply Rejection vs Frequency



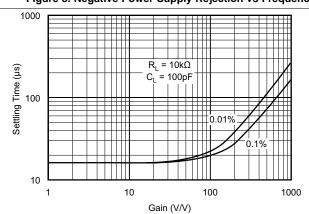
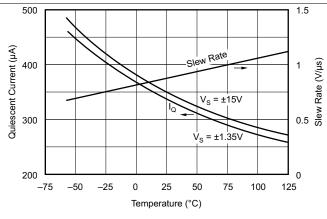


Figure 9. Input-Referred Noise Voltage vs Frequency

Figure 10. Settling Time vs Gain



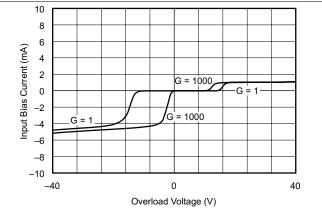


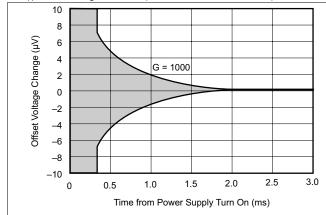
Figure 11. Quiescent Current and Slew Rate vs Temperature

Figure 12. Input Bias Current vs Input Overload Voltage



Typical Characteristics (continued)

at $T_A = 25$ °C, $V_S = \pm 15$ V (unless otherwise noted).



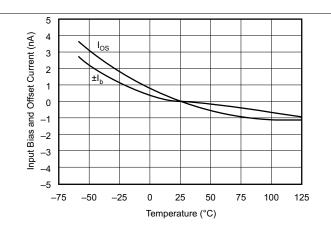


Figure 13. Offset Voltage vs Warm-Up Time

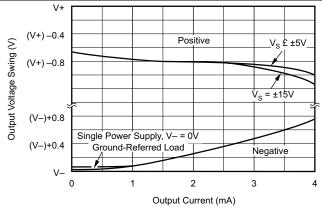


Figure 14. Input Bias and Offset Current vs Temperature

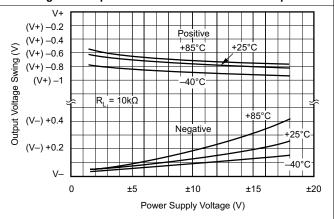


Figure 15. Output Voltage Swing vs Output Current

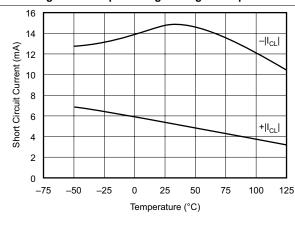


Figure 16. Output Voltage Swing vs Power Supply Voltage

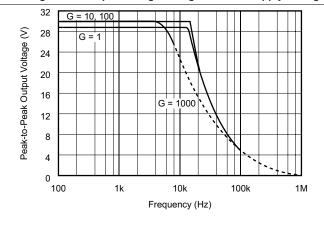


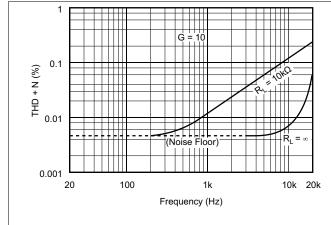
Figure 18. Maximum Output Swing vs Frequency

Figure 17. Output Current Limit vs Temperature

TEXAS INSTRUMENTS

Typical Characteristics (continued)

at $T_A = 25$ °C, $V_S = \pm 15$ V (unless otherwise noted).



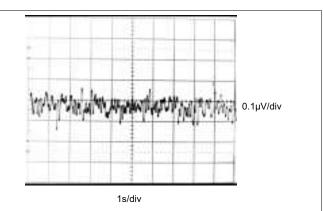
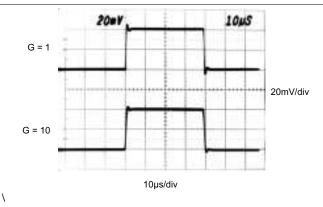


Figure 19. THD + N vs Frequency

Figure 20. Input-Referred Noise, 0.1 Hz to 10 Hz



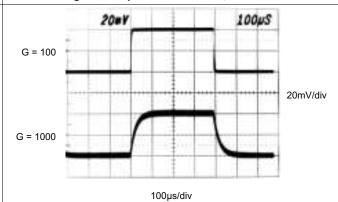
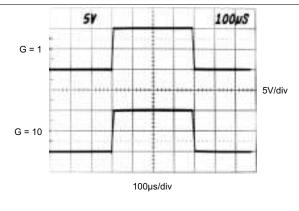


Figure 21. Small-Signal Response

Figure 22. Small-Signal Response



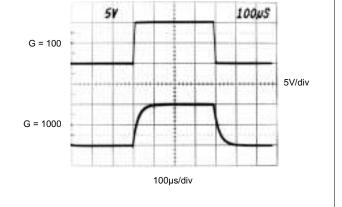


Figure 23. Large-Signal Response

Figure 24. Large-Signal Response



7 Detailed Description

7.1 Overview

Figure 25 shows a simplified representation of the INA118 and provides insight into its operation. Each input is protected by two FET transistors that provide a low series resistance under normal signal conditions, preserving excellent noise performance. When excessive voltage is applied, these transistors limit input current to approximately 1.5 to 5 mA.

The differential input voltage is buffered by Q_1 and Q_2 and impressed across R_G , causing a signal current to flow through R_G , R_1 and R_2 . The output difference amp, A_3 , removes the common-mode component of the input signal and refers the output signal to the Ref terminal.

The equations in Figure 25 describe the output voltages of A_1 and A_2 . The V_{BE} and IR drop across R_1 and R_2 produce output voltages on A_1 and A_2 that are approximately 1-V lower than the input voltages.

7.2 Functional Block Diagram

 $\begin{array}{l} A_1 \ \text{Out} = V_{\text{CM}} - V_{\text{BE}} - (10 \mu \text{A} \cdot 25 \text{k}\Omega) - V_{\text{O}}/2 \\ A_2 \ \text{Out} = V_{\text{CM}} - V_{\text{BE}} - (10 \mu \text{A} \cdot 25 \text{k}\Omega) + V_{\text{O}}/2 \\ \text{Output Swing Range } A_1, A_2; \ (V+) - 0.65 V \ \text{to} \ (V-) + 0.06 V \\ \text{Amplifier Linear Input Range:} \ (V+) - 0.65 V \ \text{to} \ (V-) + 0.98 V \end{array}$

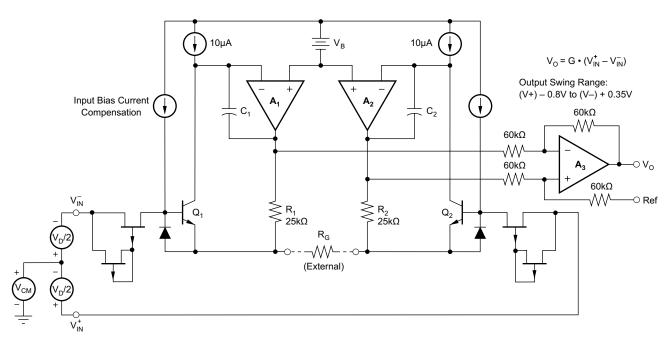


Figure 25. INA118 Simplified Circuit Diagram

7.3 Feature Description

The INA118 input sections use junction field effect transistors (JFET) connected to provide protection up to ±40 V. The current-feedback architecture provides maximum bandwidth over the full range of gain settings.

7.4 Device Functional Modes

7.4.1 Noise Performance

The INA118 provides low noise in most applications. For differential source impedances less than 1 k Ω , the INA103 may provide lower noise. For source impedances greater than 50 k Ω , the INA111 FET-Input Instrumentation Amplifier may provide lower noise.



Device Functional Modes (continued)

Low-frequency noise of the INA118 is approximately 0.28 µVp-p, measured from 0.1 to 10 Hz (G≥100). This provides dramatically improved noise when compared to state-of-the-art chopper-stabilized amplifiers.

7.4.2 Input Common-Mode Range

The linear input voltage range of the input circuitry of the INA118 is from approximately 0.6-V less than the positive supply voltage to 1-V greater than the negative supply. As a differential input voltage causes the output voltage to increase, however, the linear input range is limited by the output voltage swing of amplifiers A_1 and A_2 . Thus, the linear common-mode input range is related to the output voltage of the complete amplifier. This behavior also depends on supply voltage; see Figure 6.

Input-overload can produce an output voltage that appears normal. For example, if an input overload condition drives both input amplifiers to their positive output swing limit, the difference voltage measured by the output amplifier is near zero. The output of the INA118 is near 0 V even though both inputs are overloaded.

7.4.3 Input Protection

The inputs of the INA118 are individually protected for voltages up to ±40 V. For example, a condition of -40 V on one input and +40 V on the other input does not cause damage. Internal circuitry on each input provides low series impedance under normal signal conditions. To provide equivalent protection, series input resistors would contribute excessive noise. If the input is overloaded, the protection circuitry limits the input current to a safe value of approximately 1.5 to 5 mA. Figure 12 shows this input current limit behavior. The inputs are protected even if the power supplies are disconnected or turned off.



8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The INA118 measures a small differential voltage with a high common-mode voltage developed between the noninverting and inverting input. The high common-mode rejection makes the INA118 suitable for a wide range of applications. The ability to set the reference pin to adjust the functionality of the output signal offers additional flexibility that is practical for multiple configurations

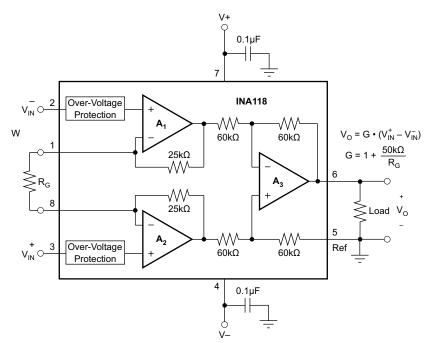
8.2 Typical Application

Figure 26 shows the basic connections required for operation of the INA118. Applications with noisy or high impedance power supplies may require decoupling capacitors close to the device pins as shown. The output is referred to the output reference (Ref) terminal, which is normally grounded. This must be a low-impedance connection to assure good common-mode rejection. A resistance of 12 Ω in series with the Ref pin causes a typical device to degrade to approximately 80-dB CMR (G = 1).

Figure 26 depicts an input signal with a 5-mV, 1-kHz signal with a 1-Vp-p common-mode signal, a condition often observed in process control systems. Figure 27 depicts the output of the INA118 (gain = 250) depicting the clean recovered 1-kHz waveform.

DESIRED GAIN	R _G (Ω)	NEAREST 1% R _G (Ω)
1	NC	NC
2	50.00k	49.9k
5	12.50k	12.4k
10	5.556k	5.62k
20	2.632k	2.61k
50	1.02k	1.02k
100	505.1	511
200	251.3	249
500	100.2	100
1000	50.05	49.9
2000	25.01	24.9
5000	10.00	10
10000	5.001	4.99

NC: No Connection.



Also drawn in simplified form:

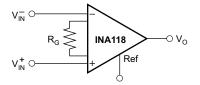


Figure 26. Basic Connections



Typical Application (continued)

8.2.1 Design Requirements

Figure 30 and Figure 29 depict the performance of a typical application of the INA118 in a shop floor vibration sensing application. Because industrial process control systems often involve the interconnecting of multiple subsystems, ground loops are frequently encountered and often are not easily solved. The inherent common-mode rejection of instrumentation amplifiers enables accurate measurements even in the presence of ground loop potentials.

The typical application was tested in a system with these requirements:

- Transducer signal ≈ 5 mVp-p
- Transducer center frequency = 1 kHz
- Common-Mode signal (required to be rejected): 1 Vp-p at 60 Hz

8.2.2 Detailed Design Procedure

8.2.2.1 Setting the Gain

As shown in Equation 1, the gain of the INA118 is set by connecting a single external resistor, R_G , connected between pins 1 and 8.

$$G=1+ \frac{50k\Omega}{R_G}$$
 (1)

Commonly used gains and resistor values are shown in Figure 26.

The 50-k Ω term in Equation 1 comes from the sum of the two internal feedback resistors of A₁ and A₂. These onchip metal film resistors are laser-trimmed to accurate absolute values. The accuracy and temperature coefficient of these resistors are included in the gain accuracy and drift specifications of the INA118.

The stability and temperature drift of the external gain setting resistor, R_G , also affects gain. The contribution of R_G to gain accuracy and drift can be directly inferred from Equation 1. Low resistor values required for high gain can make wiring resistance important. Sockets add to the wiring resistance, which contributes additional gain error (possibly an unstable gain error) in gains of approximately 100 or greater.

8.2.2.2 Dynamic Performance

The Figure 1 shows that, despite its low quiescent current, the INA118 achieves wide bandwidth, even at high gain. This is due to the current-feedback topology of the INA118. Settling time also remains excellent at high gain.

The INA118 exhibits approximately 3-dB peaking at 500 kHz in unity gain. This is a result of its current-feedback topology and is not an indication of instability. Unlike an op amp with poor phase margin, the rise in response is a predictable 6-dB/octave due to a response zero. A simple pole at 300 kHz or lower produces a flat passband unity gain response.

8.2.2.3 Offset Trimming

The INA118 is laser-trimmed for low offset voltage and drift. Most applications require no external offset adjustment. Figure 27 shows an optional circuit for trimming the output offset voltage. The voltage applied to the Ref terminal is summed at the output. The op amp buffer provides low impedance at the Ref terminal to preserve good common-mode rejection.



Typical Application (continued)

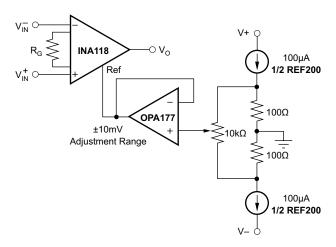


Figure 27. Optional Trimming of Output Offset Voltage

8.2.2.4 Input Bias Current Return Path

The input impedance of the INA118 is extremely high at approximately $10^{10} \Omega$. However, a path must be provided for the input bias current of both inputs. This input bias current is approximately ±5 nA. High input impedance means that this input bias current changes very little with varying input voltage.

Input circuitry must provide a path for this input bias current for proper operation. Figure 28 shows various provisions for an input bias current path. Without a bias current path, the inputs float to a potential which exceeds the common-mode range of the INA118, and the input amplifiers saturates.

If the differential source resistance is low, the bias current return path can be connected to one input (see the thermocouple example in Figure 28). With higher source impedance, using two equal resistors provides a balanced input, with the possible advantages of lower input offset voltage due to bias current, and better highfrequency common-mode rejection.

Copyright © 2000-2016, Texas Instruments Incorporated



Typical Application (continued)

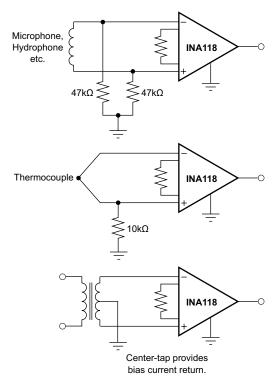
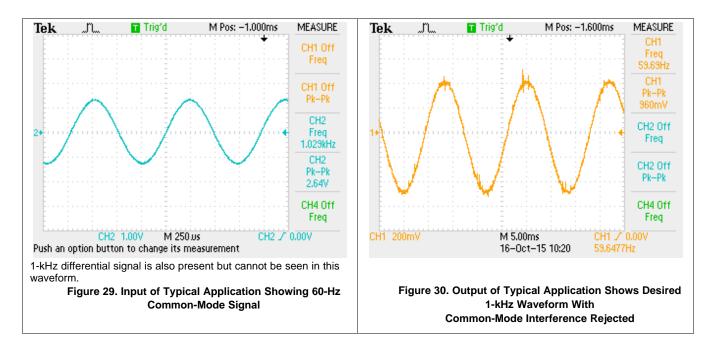


Figure 28. Providing an Input Common-Mode Current Path

8.2.3 Application Curves





9 Power Supply Recommendations

9.1 Low Voltage Operation

The INA118 can be operated on power supplies as low as ±1.35 V. Performance of the INA118 remains excellent with power supplies ranging from ±1.35 V to ±18 V. Most parameters vary only slightly throughout this supply voltage range; see *Typical Characteristics*. Operation at low supply voltage requires careful attention to assure that the input voltages remain within their linear range. Voltage swing requirements of internal nodes limit the input common-mode range with low power supply voltage. Figure 3 shows the range of linear operation for a various supply voltages and gains.

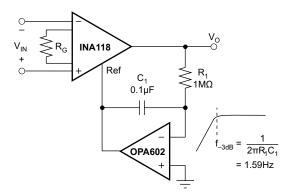
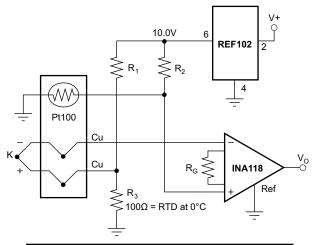


Figure 31. AC-Coupled Instrumentation Amplifier



ISA TYPE	MATERIAL	COEFFICIENT (µV/°C)	R_1, R_2
E	+ Chromel – Constantan	58.5	66.5kΩ
J	+ Iron – Constantan	50.2	76.8kΩ
К	+ Chromel – Alumel	39.4	97.6kΩ
Т	+ Copper – Constantan	38.0	102kΩ

Figure 32. Thermocouple Amplifier With Cold Junction Compensation



Low Voltage Operation (continued)

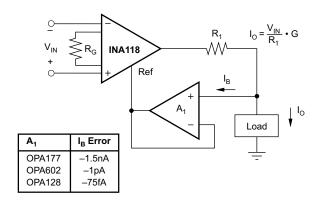


Figure 33. Differential Voltage to Current Converter

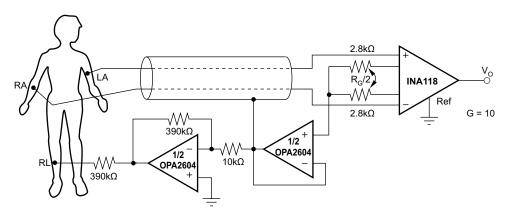


Figure 34. ECG Amplifier With Right-Leg Drive

9.2 Single Supply Operation

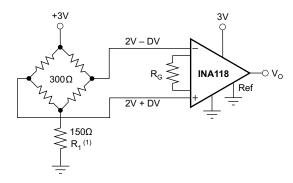
The INA118 can be used on single power supplies of 2.7 V to 36 V. Figure 35 shows a basic single supply circuit. The output Ref terminal is connected to ground. Zero differential input voltage demands an output voltage of 0 V (ground). Actual output voltage swing is limited to approximately 35-mV above ground, when the load is referred to ground as shown. Figure 15 shows how the output voltage swing varies with output current.

With single supply operation, V^+_{IN} and V^-_{IN} must both be 0.98-V above ground for linear operation. It is not possible, for example, to connect the inverting input to ground and measure a voltage connected to the noninverting input.

To illustrate the issues affecting low voltage operation, consider the circuit in Figure 35, which shows the INA118 operating from a single 3-V supply. A resistor in series with the low side of the bridge assures that the bridge output voltage is within the common-mode range of the amplifier's inputs. See Figure 3 for 3-V single supply operation.



Single Supply Operation (continued)



NOTE: (1) R_1 required to create proper common-mode voltage, only for low voltage operation — see text.

Figure 35. Single-Supply Bridge Amplifier

10 Layout

10.1 Layout Guidelines

TI always recommends paying attention to good layout practices. For best operational performance of the device, use good printed-circuit-board (PCB) layout practices, including:

- Take care to ensure that both input paths are well-matched for source impedance and capacitance to avoid converting common-mode signals into differential signals. In addition, parasitic capacitance at the gain-setting pins can also affect CMRR over frequency. For example, in applications that implement gain switching using switches or PhotoMOS® relays to change the value of RG, select the component so that the switch capacitance is as small as possible.
- Noise can propagate into analog circuitry through the power pins of the circuit as a whole, and of the device itself. Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry. Connect low-ESR, 0.1-µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V⁺ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of the circuitry is one of the simplest and most effective
 methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes.
 A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital
 and analog grounds, paying attention to the flow of the ground current. For more detailed information, see
 Circuit Board Layout Techniques (SLOA089).
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If
 these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better than in
 parallel with the noisy trace.
- Keep the traces as short as possible.



10.2 Layout Example

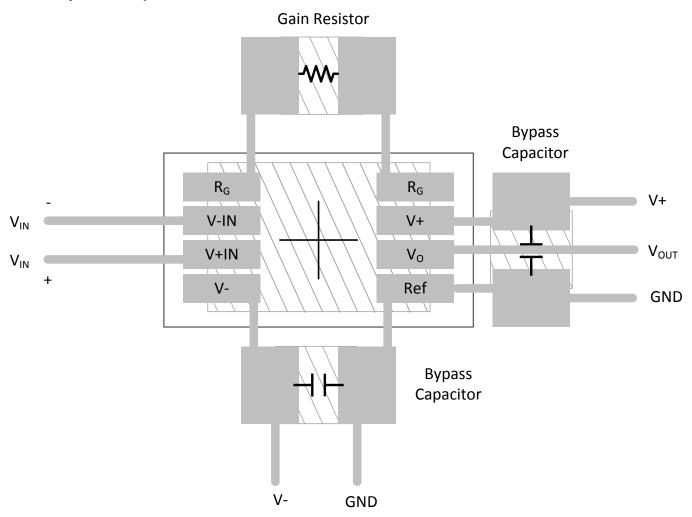


Figure 36. Layout Recommendation



11 Device and Documentation Support

11.1 Device Support

11.1.1 Development Support

Table 1. Design Kits and Evaluation Modules

NAME	PART NUMBER	TYPE
DIP Adapter Evaluation Module	DIP-ADAPTER-EVM	Evaluation Modules and Boards
Universal Instrumentation Amplifier Evaluation Module	INAEVM	Evaluation Modules and Boards

Table 2. Development Tools

NAME	PART NUMBER	TYPE			
Calculate Input Common-Mode Range of Instrumentation Amplifiers	INA-CMV-CALC	Calculation Tools			
SPICE-Based Analog Simulation Program	TINA-TI	Circuit Design and Simulation			

11.2 Documentation Support

11.2.1 Related Documentation

For related documentation, refer to the following:

Circuit Board Layout Techniques (SLOA089)

11.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.4 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

11.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

11.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Copyright © 2000–2016, Texas Instruments Incorporated





9-Apr-2015

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
INA118P	ACTIVE	PDIP	P	8	50	(2) Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type	-40 to 85	(4/5) INA118P	Sample
INA118PB	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type		INA118P B	Sample
INA118PBG4	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type		INA118P B	Sample
INA118PG4	ACTIVE	PDIP	Р	8	50	Green (RoHS & no Sb/Br)	CU NIPDAU	N / A for Pkg Type	-40 to 85	INA118P	Sample
INA118U	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR		INA 118U	Sample
INA118U/2K5	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR		INA 118U	Sample
INA118U/2K5G4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR		INA 118U	Sample
INA118UB	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR		INA 118U B	Sample
INA118UB/2K5	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR		INA 118U B	Sample
INA118UB/2K5G4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR		INA 118U B	Sample
INA118UBG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR		INA 118U B	Sampl
INA118UG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR		INA 118U	Sampl

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.



PACKAGE OPTION ADDENDUM

9-Apr-2015

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 9-Apr-2015

TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
INA118U/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
INA118UB/2K5	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

www.ti.com 9-Apr-2015



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
INA118U/2K5	SOIC	D	8	2500	367.0	367.0	35.0
INA118UB/2K5	SOIC	D	8	2500	367.0	367.0	35.0

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products Applications

Audio www.ti.com/audio Automotive and Transportation www.ti.com/automotive **Amplifiers** amplifier.ti.com Communications and Telecom www.ti.com/communications **Data Converters** dataconverter.ti.com Computers and Peripherals www.ti.com/computers **DLP® Products** www.dlp.com Consumer Electronics www.ti.com/consumer-apps DSP dsp.ti.com **Energy and Lighting** www.ti.com/energy Clocks and Timers www.ti.com/clocks Industrial www.ti.com/industrial Interface interface.ti.com Medical www.ti.com/medical Logic Security www.ti.com/security logic.ti.com

Power Mgmt power.ti.com Space, Avionics and Defense www.ti.com/space-avionics-defense

Microcontrollers <u>microcontroller.ti.com</u> Video and Imaging <u>www.ti.com/video</u>

RFID www.ti-rfid.com

OMAP Applications Processors <u>www.ti.com/omap</u> TI E2E Community <u>e2e.ti.com</u>

Wireless Connectivity www.ti.com/wirelessconnectivity